Most Frequently Occurring Classifications of Patents Returned
From A Search of 09/990,330 on October 04, 2002

Combined Classifications

6 257/133
6 257/138
6 257/E29.214
6 257/E29.216
6 438/305
5 257/E29.257
4 257/378
4 257/412
4 257/E29.04
4 257/E29.066
4 438/270
3 257/137
3 257/139
3 257/146
3 257/163
3 257/316
3 257/331
3 257/339
3 257/341
3 257/350
3 257/401
3 257/E29.063
3 438/234
3 438/302
3 438/307
2 257/132
2 257/142
2 257/144
2 257/147
2 257/154
2 257/157
2 257/173
2 257/322
2 257/324
2 257/330
2 257/332
2 257/336
2 257/340
2 257/342
2 257/344
2 257/348
2 257/402
2 257/409
2 257/413
2 257/E29.008
2 257/E29.027
2 257/E29.054
2 257/E29.055
2 257/E29.133
2 257/E29.201
2 257/E29.26
2 257/E29.268

2 257/E29.275
2 438/230
2 438/259
2 438/261
2 438/301
2 438/303
2 438/525
2 438/586
2 438/595
2 438/981

6 257/133 (1 OR, 5 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/107 (E) REGENERATIVE TYPE SWITCHING DEVICE (E.G., SCR, COMFET, THYRISTOR)
257/133 .(E) Combined with field effect transistor

6 257/138 (2 OR, 4 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/107 (E) REGENERATIVE TYPE SWITCHING DEVICE (E.G., SCR, COMFET, THYRISTOR)
257/133 .(E) Combined with field effect transistor
257/137 ..(E) Having controllable emitter shunt
257/138 ...(E) Having gate turn off (GTO) feature

6 257/E29.214 (0 OR, 6 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E29.162 ....Insulating materials for IGFET (EPO)
257/E29.166 .Types of semiconductor semiconductor device (EPO)
257/E29.169 ..Controllable by only signal applied to control electrode (e.g., base of bipolar transistor, gate of field effect transistor) (EPO)
257/E29.171 ...Bipolar device (EPO)
257/E29.211 ....Thyristor-type device (e.g., having four-zone regenerative action) (EPO)
257/E29.212 .....Gate-turn-off device (EPO)
257/E29.213 .....With turn off by field effect (EPO)
257/E29.214 .....Produced by insulated gate structure (EPO)

6 257/E29.216 (0 OR, 6 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E29.162 ....Insulating materials for IGFET (EPO)
257/E29.166 .Types of semiconductor semiconductor device (EPO)
257/E29.169 ..Controllable by only signal applied to control electrode (e.g., base of bipolar transistor, gate of field effect transistor) (EPO)
257/E29.171 ...Bipolar device (EPO)
257/E29.211 ....Thyristor-type device (e.g., having four-zone regenerative action) (EPO)
257/E29.216 .....With turn on by field effect (EPO)

6 438/305 (1 OR, 5 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION OR ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
438/197 .Having insulated gate (e.g., IGFET, MISFET, MOSFET, etc.)
438/299 ..Self-aligned
438/301 ...Source or drain doping
438/303 ....Utilizing gate sidewall structure
438/305 .....Plural doping steps

5 257/E29.257 (0 OR, 5 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E29.162 ....Insulating materials for IGFET (EPO)
257/E29.166 .Types of semiconductor semiconductor device (EPO)
257/E29.169 ..Controllable by only signal applied to control electrode (e.g., base of bipolar transistor, gate

of field effect transistor) (EPO)
257/E29.226 ...Unipolar device (EPO)
257/E29.242 ....Field effect transistor (EPO)
257/E29.255 .....With field effect produced by insulated gate (EPO)
257/E29.256 .....With channel containing layer contacting drain drift region (e.g., DMOS transistor) (EPO)
257/E29.257 .....Having a vertical bulk current component or current vertically following a trench gate, (e.g., vertical power DMOS transistor) (EPO)

4 257/378 (0 OR, 4 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 (E) FIELD EFFECT Device
257/288 .(E) Having insulated electrode (e.g., MOSFET, MOS diode)
257/368 ..(E) Insulated gate field effect transistor in integrated circuit
257/378 ...Combined with bipolar transistor

4 257/412 (2 OR, 2 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/213 (E) FIELD EFFECT Device
257/288 .(E) Having insulated electrode (e.g., MOSFET, MOS diode)
257/412 ..Gate electrode of refractory material (e.g., polysilicon or silicide of a refractory or platinum group metal)

4 257/E29.04 (0 OR, 4 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E29.001 DETAILS OF SEMICONDUCTOR BODIES OR ELECTRODES OF SEMICONDUCTOR DEVICES ADAPTED FOR RECTIFYING, AMPLIFYING, OSCILLATING OR SWITCHING, OR CAPACITORS OR RESISTORS WITH AT LEAST ONE POTENTIAL-JUMP BARRIER OR SURFACE BARRIER (E.G., PN JUNCTION DEPLETION LAYER OR CARRIER CONCENTRATION LAYER) (EPO)
257/E29.002 .Electrical characteristics due to properties of entire semiconductor body rather than just surface region (EPO)
257/E29.005 ..Characterized by specified shape or size of PN junction or by specified impurity concentration gradient within device (EPO)
257/E29.029 ...With semiconductor regions connected to electrode carrying current to be rectified, amplified, or switched and such electrode being part of semiconductor device which comprises three or more electrodes (EPO)
257/E29.039 ....Source or drain regions of field-effect devices (EPO)
257/E29.04 .....Of field-effect transistors with insulated gate (EPO)

4 257/E29.066 (0 OR, 4 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
257/E29.001 DETAILS OF SEMICONDUCTOR BODIES OR ELECTRODES OF SEMICONDUCTOR DEVICES ADAPTED FOR RECTIFYING,

PLUS Search Results for S/N 09/990,330, Searched October 04, 2002 (Top 50)

5736767	5324966	6087237	4914496	5457061
5314834	5654215	6087224	4983538	5460988
5840604	5804476	6096586	5200354	5463237
5918114	5834352	6110788	5208477	5471075
6040212	5885859	6140688	5250447	5488236
6051509	5894150	6228698	5279979	5554862
6222232	6002154	4358890	5296726	5580799
6222232	6001695	4417385	5336943	5604368
5221850	6037631	4760431	5414287	5610430
5241194	6080630	4908682	5444272	5625213